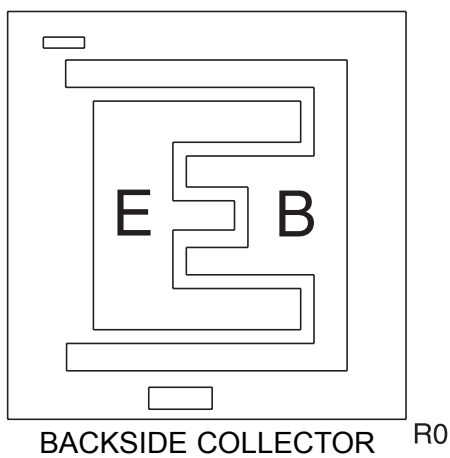


#### PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	31.5 x 31.5 MILS
Die Thickness	11 MILS
Base Bonding Pad Area	7.8 x 6.2 MILS
Emitter Bonding Pad Area	8.0 x 5.3 MILS
Top Side Metalization	Al - 12,000Å
Back Side Metalization	Au - 10,000Å

#### GEOMETRY



#### GROSS DIE PER 4 INCH WAFER

11,380

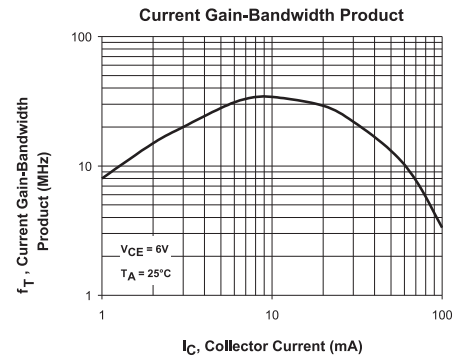
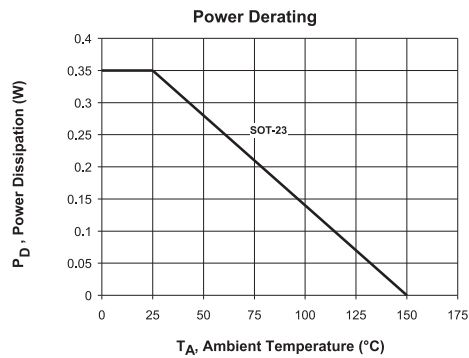
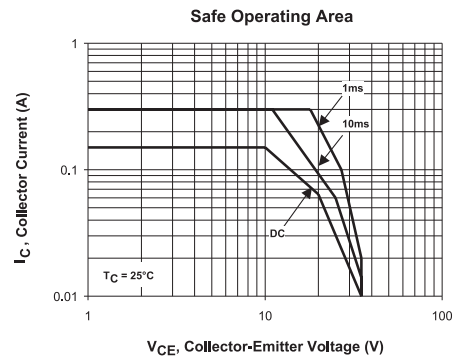
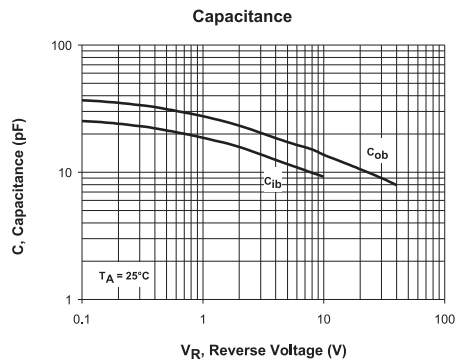
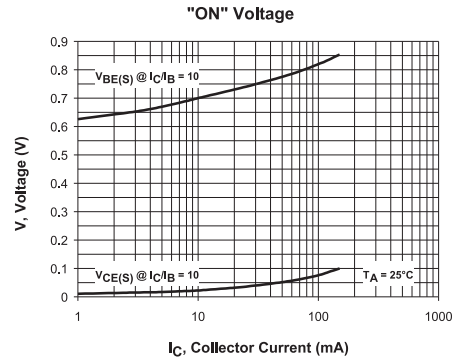
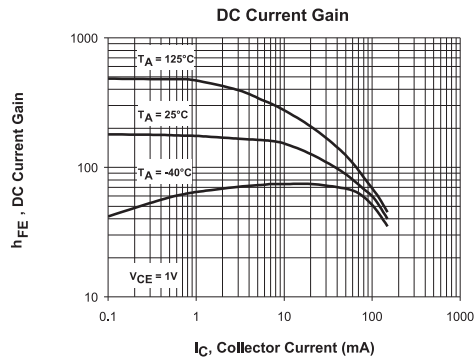
#### PRINCIPAL DEVICE TYPES

CMPT404A

MPS404A

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
[www.centrasemi.com](http://www.centrasemi.com)

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